

CLAIMS

Claims 1-17. (Cancelled)

18. (Currently Amended) A thin film magnetic memory device, comprising:

a memory array having a plurality of memory cells arranged in a matrix, each memory cell having an electric resistance that varies according to storage data magnetically written there, said memory array being divided into a plurality of memory blocks along a direction of the memory cell rows; and

a plurality of write digit lines arranged respectively corresponding to said plurality of memory cell rows, for passing therethrough a prescribed write current of a fixed direction in a selected row in data write operation;

a plurality of bit lines arranged respectively corresponding to the plurality of memory cell columns, wherein in each memory cell column, said bit line is divided by said plurality of memory blocks,

said thin film magnetic memory device further comprising:

a plurality of column selection lines arranged respectively corresponding to said plurality of memory cell columns, for transmitting a column selection result, each column selection line being provided to extend along a direction of the memory cell columns and shared by said plurality of memory blocks; and

a plurality of write drivers provided respectively corresponding to said plurality of bit lines in regions adjacent to each of said memory blocks in the direction of the memory cell columns, each write driver operating in response to activation of a corresponding one of said plurality of column selection lines to supply a data write current of a direction corresponding to a level of write data to a corresponding one of said plurality of bit lines.